

General Clock Generator

PRODUCT DESCRIPTION

MS5351M is an I²C configurable, 3-channel output clock generator chip, which can completely replace crystals, crystal oscillators, phase-locked loops, and output buffers used in cost-sensitive applications. Thanks to the use of fractional frequency phase locked loop and high-precision fractional frequency divider structure, MS5351M can generate any clock output from 2.5kHz to 200MHz.

FEATURES

- Highly integrated analog circuit to demodulate and decode
- 3 channels output non-integer related clocks from 2.5kHz to 200MHz
- I²C user-defined configuration output clock
- Accurate frequency synthesis
- Low output jitter
- Can work with low-cost, fixed-frequency quartz crystals: 25MHz or 27MHz
- Output clock supports static phase shift
- Programmable control of output clock rise/fall time
- Glitch-free frequency switching
- Independent power supply pins Internal core circuit power supply VDD:

2.5V or 3.3V Output stage

- High internal power supply rejection ratio can save external filter capacitor
- Adjustable output delay
- Compatible with HCSL and PCIE Gen 1 applications

APPLICATIONS

- HD TV, DVD/Blu-ray, set-top box
- Audio/video equipment, Game consoles
- Printers, scanners, projectors
- Hand-held devices
- Home gateway equipment
- Network/communication
- Servers, storage
- Quartz crystal/crystal oscillator/phase-locked loop replacement

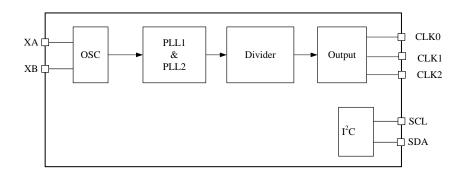
PACKAGE/ORDERING INFORMATION

Part Number	Package	Marking
MS5351M	MSOP10	MS5351M



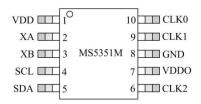


SIMPLIFIED BLOCK DIAGRAM





PIN CONFIGURATIONS



Pin	Symbol	Туре	Description
1	VDD	power	Internal circuit power supply
2	XA	input	External quartz crystal input
3	XB	input	External quartz crystal input
4	SCL	input	I^2C clock input, at least 1k Ω pull-up resistor must be connected
5	SDA	input/output	$\mbox{I}^2\mbox{C}$ data input/output, at least 1k Ω pull-up resistor must be connected
6	CLK2	output	Output clock
7	VDDO	power	Output stage power supply
8	GND	ground	Reference GND
9	CLK1	output	Output clock
10	CLK0	output	Output clock



ABSOLUTE MAXIMUM RATINGS

Note: It is not allowed to exceed the range of rated value in actual application. [1]

Table 1. Limiting Condition.

Parameter	Symbol	Condition	Rated value	Unit
Internal supply voltage	VDD		-0.5 to 3.8	V
Output stage supply voltage	VDDO		-0.5 to 3.8	V
Input pin voltage	VIN_SCL	SCL,SDA	-0.5 to 3.8	V
	VIN_XA/XB	XA,XB	-0.5 to 1.3	V
Junction temperature	TJ		-55 to 150	°C
Soldering iron temperature (lead-free) [2]	T _{PEAK}		260	°C
Duration of soldering iron temperature at T _{PEAK} (lead-free) [2]	T _P		10	Second

^[1] Exceeding the absolute rated maximum value may cause permanent damage to the chip

^[2] The chip meets the JEDEC J-STD-020 specification



RECOMMEND OPERATING CONDITION

Table 2.Operating Condition

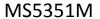
Symbol	Parameter	Min	Тур	Max	Unit
Operating temperature	T_A	-40	25	105	°C
Internal circuit voltage	VDD	3.0	3.3	3.6	V
		2.25	2.5	2.75	V
Output stage voltage	VDDO	1.71	1.8	1.89	V
		2.25	2.5	2.75	V



ELECTRICAL CHARACTERISTICS

Table 3. Electrical characteristics (VCC=3.3V, TA = 25° C, unless otherwise noted.)

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Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit		
DC Characteristic		2 shannel sutmut		22		1		
VDD Current	I _{DD}	3 channel output		33		mA		
Single channel output	I _{DDOx}	C _L =5pF, Less than 100MHz		5		mA		
stage current	_	Maximum drive capacity				_		
Input Current	I _{SCL}	SCL,SDA			10	uA		
Output impedance	Z _O	3.3V VDDO,High drive		50		Ω		
AC Characteristic		<u> </u>			I	1		
Power-on time	T_{RDY}	From VDDmin to effective output		2	10	ms		
		clock, f _{CLKn} >1MHz						
Power-on time when	T_{BYP}	From VDDmin to effective output		0.5	1	ms		
PLL bypass		clock, f _{CLKn} >1MHz						
Output frequency	T_{FREQ}	f _{CLKn} >1MHz			20	us		
switching time								
Output phase shift	P_{STEP}			333		ps/ste		
						р		
Spread spectrum range	SS_DEV	Down spread spectrum, 0.1% per	-0.1		-2.5	%		
		step						
		Center spread spectrum, 0.1% per	±0.1		±2.5	%		
		step						
Spread spectrum	SS _{MOD}		30	31.5	33	kHz		
modulation rate								
Crystal specifications								
Quartz crystal	f_{XTAL}		25		27	MHz		
frequency								
Load capacitance	C _{XL}		6		12	pF		
Equivalent series	r _{ESR}				150	Ω		
resistance								
Maximum drive level	d_L		100			uW		
Input voltage	V _{IN_XA/AB}	XA and XB	-0.3		1.1	V		
Output clock specificatio								
Output frequency	F _{CLK}		0.0025		200	MHz		
Load capacitance	C _L				15	pF		
Duty cycle	DC	F _{CLK} <160MHz	45	50	55	%		
, ,								
		F _{CLK} <160MHz	40	50	60	%		
Rise Time	t _r	20%~80%,C _L =5pFMaximum drive		0.5	1.2	ns		
Fall time	t _f	20%~80%,C _L =5pFMaximum drive		0.5	1.2	ns		
Output high level	V_{OH}	C _L =5pF	VDD-					
			0.6					





Output low level			V _{OL}	C _L =5pF					0.6	
Period jitter		J _{PER} 3		3 channels si	3 channels simultaneously output			60	180	ps,pk
Adjacent clock jitter			J_{CC}	3 channels si	multaneously	output		60	180	ps,pk
I ² C Specification (S	CL, SDA	A)								
Parameter	Syml	bol	Conditio	n	Standard mode		Fast mode		Unit	
					100	100kbps		400kbps		
					Min.	Max.	Min	١.	Max.	V
Low-level input	V _{ILI2C}	,			-0.5	0.3*V _{DDI2C}	-0.5	5	0.3*V _{DDI2C}	V
voltage										
High-level input	V _{IHI2C}	()			0.7*V _{DDI2C}	3.6	0.7*V ₀	DDI2C	3.6	V
voltage										
Schmidt hysteresis	V _{HYS}				-	-	0.1		-	V
voltage										
Low-level output	V _{OLI20}	C	V _{OLI2C} =2.	5/3.3V,	0	0.4	0		0.4	V
voltage			Open dr	ain, 3mA						
current		current	sink							
Input Current	I _{II2C}				-10	10	-10)	10	uA
Pin capacitance	C _{I2C}		VIN=-0.1	toV _{DDI2C}	-	4	-		4	pF
I ² CBus pause time	T _{TO}		Pause er	nable	25	35	25		35	ms

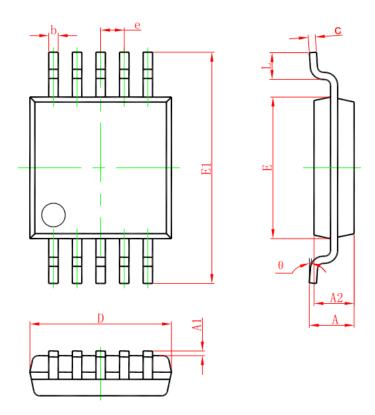
Version number: V1.0

NOTE:

- [1] Only 2 clocks larger than 112.5MHz are allowed to be output at the same time
- [2] The clock jitter test is 10000 cycles, and measured at the maximum output drive capacity
- [3] Jitter is highly dependent on frequency configuration
- [4] I²C only supports 2.25V to 3.6V power supply



PACKAGE OUTLINE DIMENSIONS

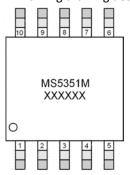


Comb a I	Dimensions In	n Millimeters	Dimensions	In Inches	
Symbol	Symbol Min		Min	Max	
Α	0. 820	1. 100	0. 032	0. 043	
A1	0. 020	0. 150	0. 001	0. 006	
A2	0. 750	0. 950	0. 030	0. 037	
b	0. 180	0. 280	0. 007	0. 011	
С	0.090	0. 230	0. 004	0.009	
D	2. 900	3. 100	0. 114	0. 122	
е	0.50(BSC)	0.020	(BSC)	
E	2. 900	3. 100	0. 114	0. 122	
E1	4. 750	5. 050	0. 187	0. 199	
L	0. 400	0.800	0. 016	0. 031	
θ	0°	6°	0°	6°	



Marking and Packaging Specifications

1. Marking drawing description



MS5351M: Product name XXXXXX: Product code

2. Marking drawing pattern

Laser printing, contents in the middle, font type Arial.

3. Packaging Specifications

Device	Package	piece/reel	reel/box	piece /box	box/carton	piece/carton
MS5351M	MSOP10	3000	1	3000	8	24000





MOS circuit operation precautions:

Static electricity can be generated in many places. The following precautions can be taken to effectively prevent the damage of MOS circuit caused by electrostatic discharge:

- 1. The operator shall ground through the anti-static wristband.
- 2. The equipment shell must be grounded.
- 3. The tools used in the assembly process must be grounded.
- 4. Must be used conductor packaging or antistatic materials packaging or transportation.

